

ZVP3306A Information



For Reference Only

Part Number ZVP3306A

Manufacturer Diodes Incorporated

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET P-CH 60V 160MA TO92-3 **Package** TO-226-3, TO-92-3 (TO-226AA)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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Certified Quality

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ZVP3306A Specifications

Manufacturer Part Number ZVP3306A Manufacturer Diodes Incorporated Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 160mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ ImA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA) Report errors?		
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) four - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ### 20V ### 31A On (Max) ### 32 On (Max) @ Id, Vgs ### 33 On (Max) @ Id, Vgs ### 34 On (Max) @ Id, Vgs ### 35 On (Max) @ Id, Vgs ### 36 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 38 On (Max) @ Id, Vgs ### 39 On (Max) @ Id, Vgs ### 30 On (Max) @ Id, Vgs ### 30 On (Max) @ Id, Vgs ### 31 On (Max) @ Id, Vgs ### 31 On (Max) @ Id, Vgs ### 32 On (Max) @ Id, Vgs ### 31 On (Max) @ Id, Vgs ### 32 On (Max) @ Id, Vgs ### 31 On (Max) @ Id, Vgs ### 32 On (Max) @ Id, Vgs ### 31 On (Max) @ Id, Vgs ### 31 On (Max) @ Id, Vgs ### 32 On (Max) @ Id, Vgs ### 33 On (Max) @ Id, Vgs ### 34 On (Max) @ Id, Vgs ### 35 On (Max) @ Id, Vgs ### 35 On (Max) @ Id, Vgs ### 36 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 38 On (Max) @ Id, Vgs ### 38 On (Max) @ Id, Vgs ### 38 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 38 On (Max) @ Id, Vgs ### 37 On (Max) @ Id, Vgs ### 38 On (Max) @ Id, Vgs ### 39 On (Max) @ Id, Vgs ### 30 On (Max) @ Id	Manufacturer Part Number	ZVP3306A
Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 160mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-A, TO-92-3 (TO-226AA)	Manufacturer	Diodes Incorporated
Package TO-226-3, TO-92-3 (TO-226AA) Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 160mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Category	Discrete Semiconductor Products
Series - FET Type P-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 60V Current - Continuous Drain (Id) @ 25°C 160mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 (TO-226AA)		Transistors - FETs, MOSFETs - Single
FET TypeP-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C160mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds50pF @ 18VVgs (Max)±20VFET Feature-Power Dissipation (Max)625mW (Ta)Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Package	TO-226-3, TO-92-3 (TO-226AA)
Technology Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 160mA (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) **EUV** FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature - 55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case **To-92-3 (TO-226AA)	Series	-
Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C160mA (Ta)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id3.5V @ 1mAGate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds50pF @ 18VVgs (Max)±20VFET Feature-Power Dissipation (Max)625mW (Ta)Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Type	P-Channel
Current - Continuous Drain (Id) @ 25°C 160mA (Ta) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature Supplier Device Package Package / Case TO-92-3 TO-92-3 (TO-226AA)	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id 3.5V @ 1mA Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds 50pF @ 18V Vgs (Max) ±20V FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Current - Continuous Drain (Id) @ 25°C	160mA (Ta)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature Jenses Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±20V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs(th) (Max) @ Id	3.5V @ 1mA
Vgs (Max)±20VFET Feature-Power Dissipation (Max)625mW (Ta)Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature - Power Dissipation (Max) 625mW (Ta) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Input Capacitance (Ciss) (Max) @ Vds	50pF @ 18V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 14 Ohm @ 200mA, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Vgs (Max)	±20V
Rds On (Max) @ Id, Vgs14 Ohm @ 200mA, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-92-3Package / CaseTO-226-3, TO-92-3 (TO-226AA)	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Power Dissipation (Max)	625mW (Ta)
Mounting Type Through Hole Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Rds On (Max) @ Id, Vgs	14 Ohm @ 200mA, 10V
Supplier Device Package TO-92-3 Package / Case TO-226-3, TO-92-3 (TO-226AA)	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-226-3, TO-92-3 (TO-226AA)	Mounting Type	Through Hole
	Supplier Device Package	TO-92-3
Report errors?	Package / Case	TO-226-3, TO-92-3 (TO-226AA)
		Report errors?

ZVP3306A Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

ZVP3306A Payment Methods



















ZVP3306A Shipping Methods













If you have any question about ZVP3306A, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com